



60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-15 A

Features

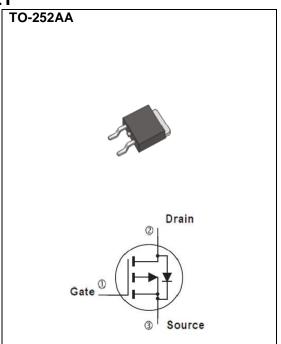
- R_{DS(ON)}, V_{GS}@-10V,I_D@-7.5A<68mΩ
- R_{DS(ON)}, V_{GS}@-4.5V,I_D@-4.0A<85mΩ
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0105 ounces, 0.297 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	-60	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	Tc=25°C	I _D	-15	A	
	T _C =100°C		-9.5		
Pulsed Drain Current(Note 1)	Tc=25°C	I _{DM}	-60		
Power Dissipation	T _C =25°C	Po	25	W	
	Tc=100°C		10		
Continuous Drain Current	T _A =25°C	Ι _D	-4.0	А	
	T _A =70°C		-3.2	А	
Power Dissipation	T _A =25°C	-	2.0	W	
Power Dissipation	T _A =70°C	Pb	1.3		
Single Pulse Avalanche Energy(Note 6)		E _{AS}	31	mJ	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance	Junction to Case	$R_{ heta JC}$	5.0	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =-250uA	-60	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =-250uA	-1.0	-1.63	-2.5	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V,I _D =-7.5A	-	55	68	mO	
Dialii-Source Oil-State Resistance		V _{GS} =-4.5V,I _D =-4.0A	-	73	85	mΩ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V,V _{GS} =0V	-	-	-1.0	uA	
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic ^(Note 7)							
Total Gate Charge	Q_g		-	17	-	nC	
Gate-Source Charge	Qgs	V_{DS} =-30V, I_{D} =-7.5A, V_{GS} =-10V ^(Note 3)	-	2.8	-		
Gate-Drain Charge	Q_{gd}	VGS=-10 V (100 5)	-	3.6	-		
Input Capacitance	Ciss		-	879	-	pF	
Output Capacitance	Coss	V _{DS} =-30V, V _{GS} =0V, f=1.0MHZ	-	70	-		
Reverse Transfer Capacitance	Crss	I=1.0IVII IZ	-	47	-		
Turn-On Delay Time	td _(on)	.,	-	8.4	-		
Turn-On Rise Time	V _{DD} =-30V, I _D =-1A,		-	30	-		
Turn-Off Delay Time	td _(off)	V_{GS} =-10V, R_{G} =6Ω (Note 3)	-	52	-	ns	
Turn-Off Fall Time	t _f	(13333)	-	16	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	Is				-15	Α	
Diode Forward Current	IS			-	-10	Α	
Diode Forward Voltage	V_{SD}	I _S =-1A,V _{GS} =0V	-	-0.73	-1.0	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
- 6. L=0.1mH, I_{AS} =-25A, V_{GS} =-10V, V_{DS} =-25V, R_{G} =25 ohm
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

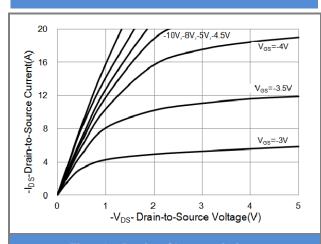


Fig.1 On-Region Characteristics

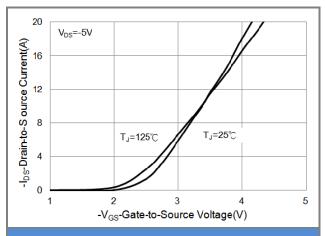


Fig.2 Transfer Characteristics

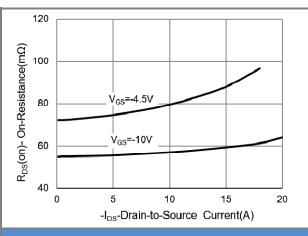


Fig.3 On-Resistance vs. Drain Current

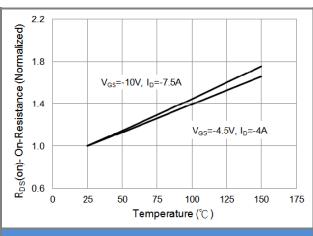
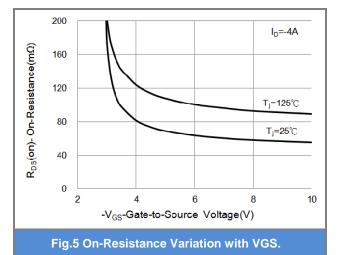
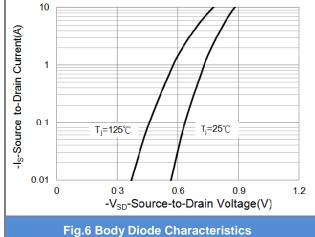


Fig.4 On-Resistance vs. Junction temperature









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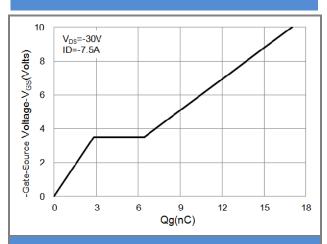


Fig.7 Gate-Charge Characteristics

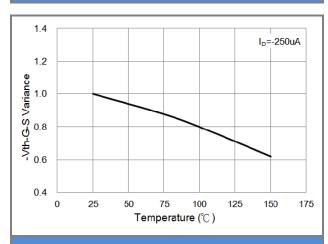
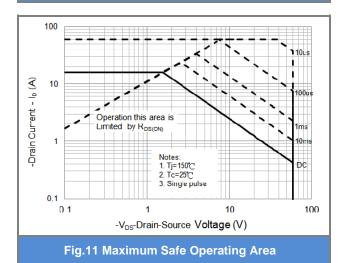


Fig.9 Threshold Voltage Variation with Temperature



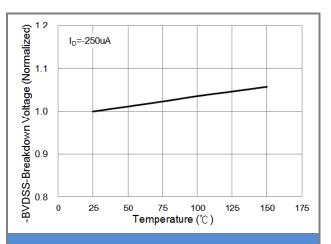


Fig.8 Breakdown Voltage Variation vs. Temperature

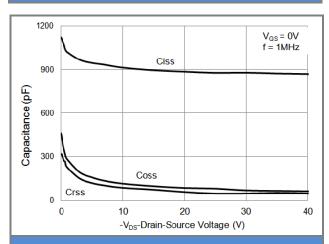


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

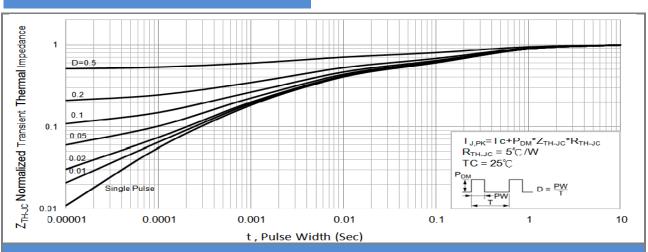
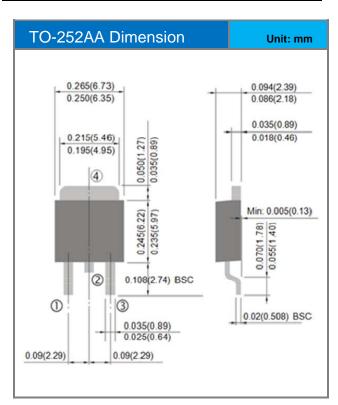


Fig.12 Normalized Thermal Transient Impedance





Packaging Information



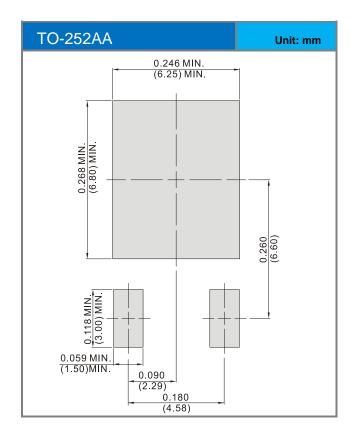




PART NO. PACKING CODE VERSION

Part No. Packing Code	Package Type	Packing Type	Marking	Version	
PJD15P06A_L2_00001	TO-252AA	3,000pcs / 13" reel	D15P06A	Halogen free	

MOUNTING PAD LAYOUT







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